SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		31		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.1		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 250 µA	1.2		2.4	V
Gate Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	20			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 7.5 A		0.018	0.022	Ω
		V_{GS} = 4.5 V, I_D = 6.5 A		0.022	0.027	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 7.5 A		20		S
Dynamic[a]						
Input Capacitance	C_{iss}	N-Channel V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		865		pF
Output Capacitance	C_{oss}			131		
Reverse Transfer Capacitance	C_{rss}			66		
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 7.5 A		15.4	23	nC
		N-Channel V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 7.5 A		7	10.5	
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			2.2		
Gate Resistance	R_g	f = 1 MHz	0.4	1.9	3.8	Ω
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 15 V, R_L = 3 Ω $I_D \cong$ 5 A, V_{GEN} = 10 V, R_g = 1 Ω		9	18	ns
Rise Time	t_r			12	24	
Turn-Off Delay Time	$t_{d(off)}$			17	34	
Fall Time	t_f			9	18	
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 15 V, R_L = 3 Ω $I_D \cong$ 5 A, V_{GEN} = 4.5 V, R_g = 1 Ω		17	34	
Rise Time	t_r			13	26	
Turn-Off Delay Time	$t_{d(off)}$			19	35	
Fall Time	t_f			9	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			2.4	A
Pulse Diode Forward Current[a]	I_{SM}				30	
Body Diode Voltage	V_{SD}	I_S = 1.8 A		0.77	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	N-Channel I_F = 5 A, dI/dt = 100 A/µs, T_J = 25 °C		16	32	ns
Body Diode Reverse Recovery Charge	Q_{rr}			8	16	nC
Reverse Recovery Fall Time	t_a			10		ns
Reverse Recovery Rise Time	t_b			6		

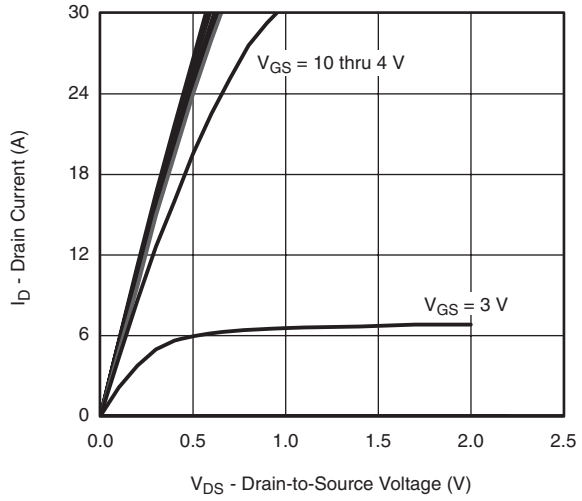
Notes:

a. Guaranteed by design, not subject to production testing.

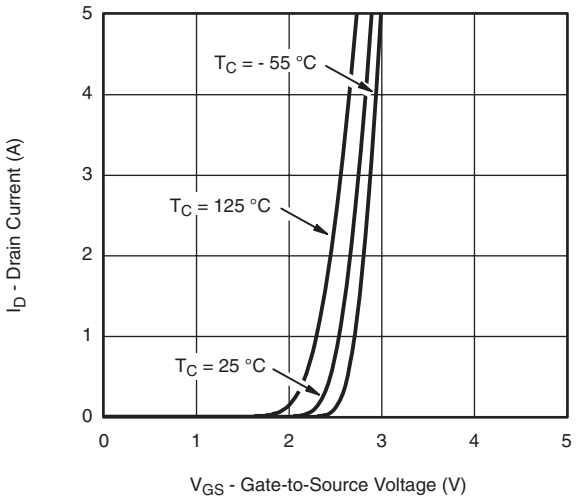
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

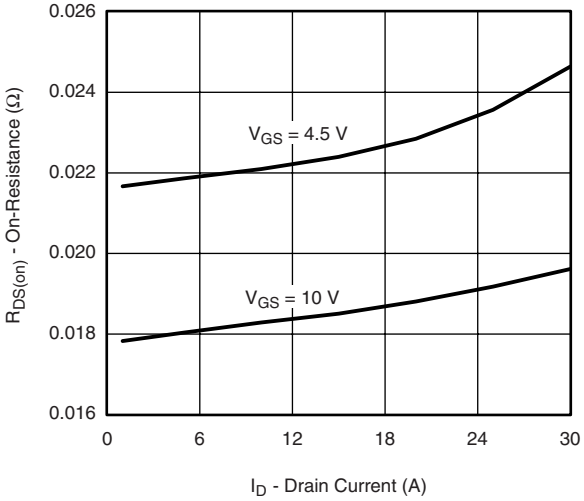
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



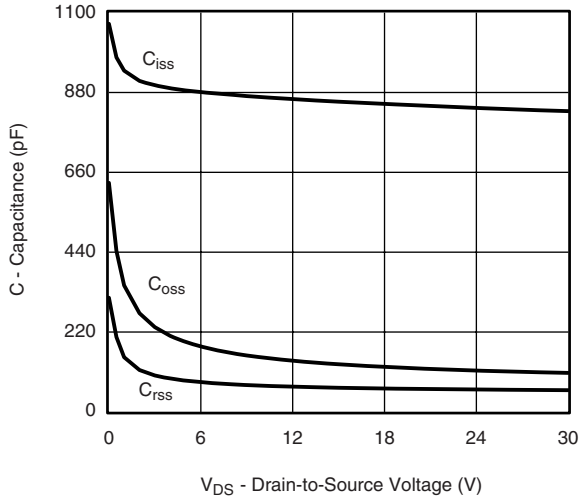
Output Characteristics



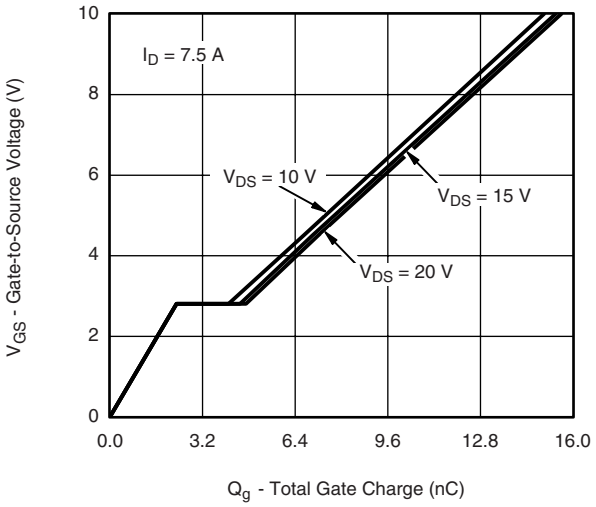
Transfer Characteristics



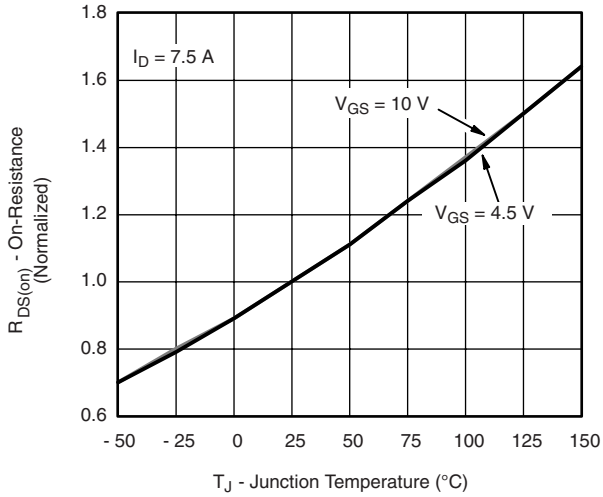
On-Resistance vs. Drain Current



Capacitance

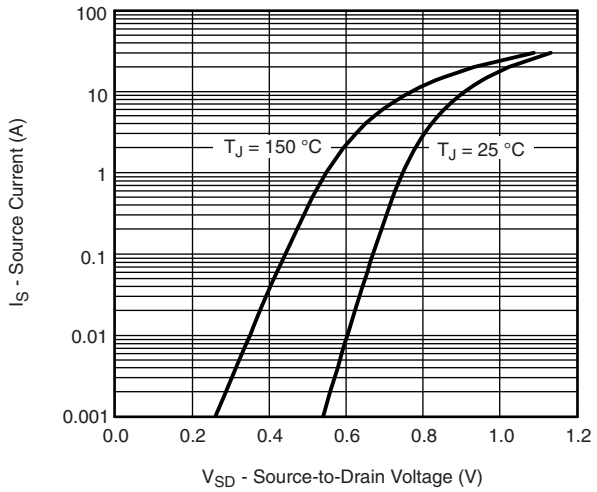


Gate Charge

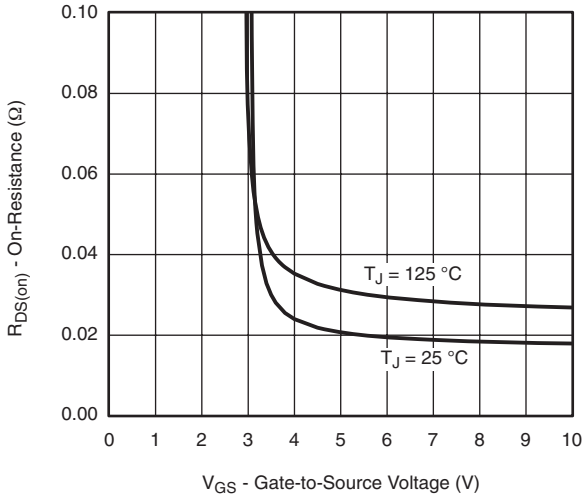


On-Resistance vs. Junction Temperature

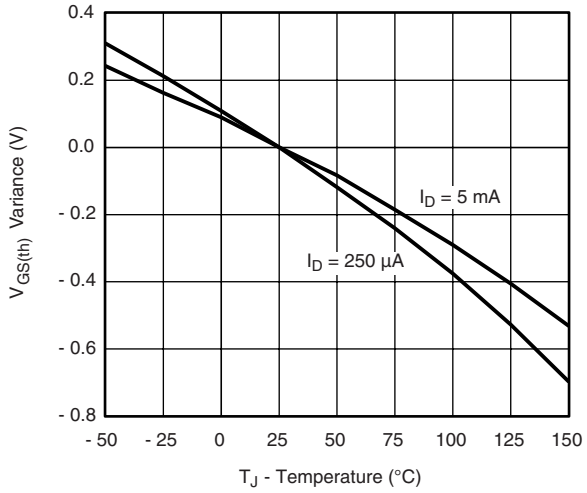
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



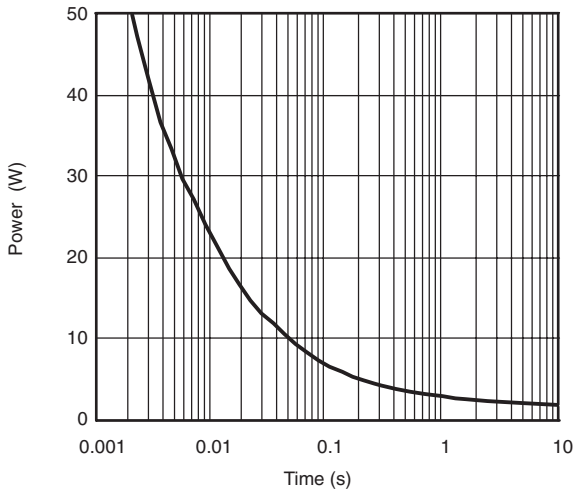
Source-Drain Diode Forward Voltage



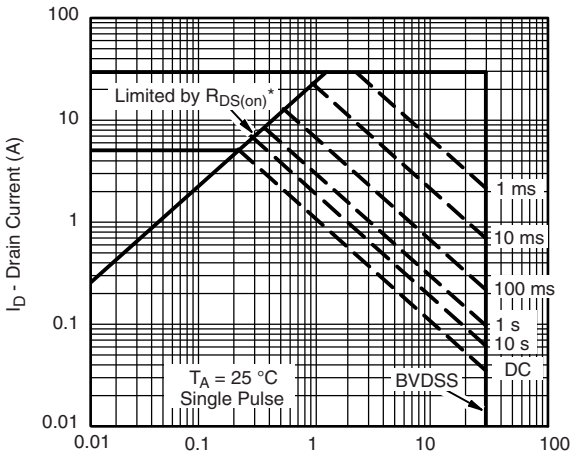
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



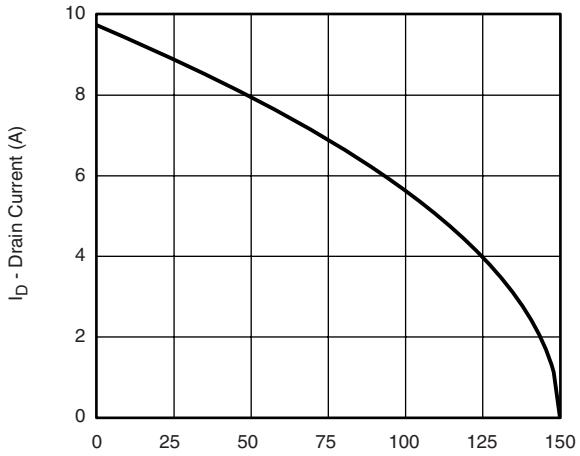
Single Pulse Power, Junction-to-Ambient



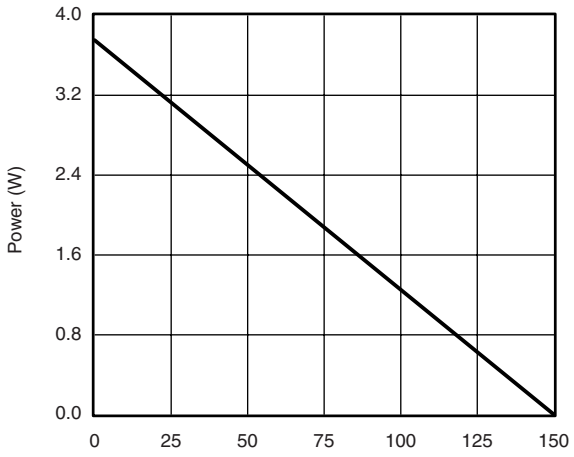
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

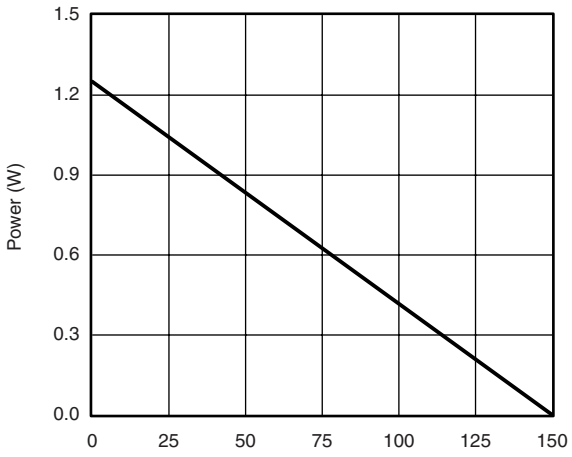
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



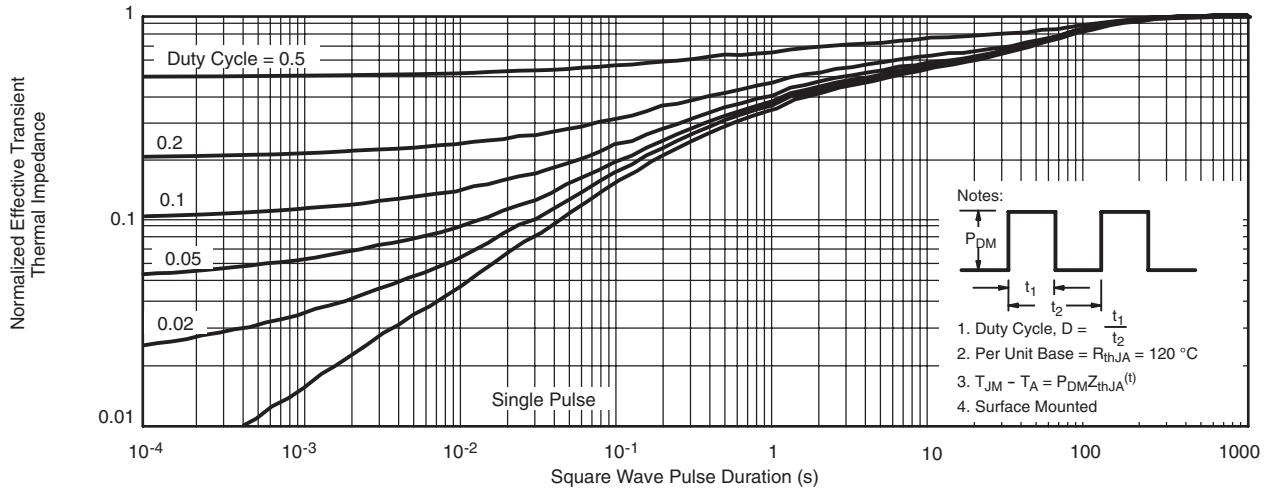
Power, Junction-to-Foot



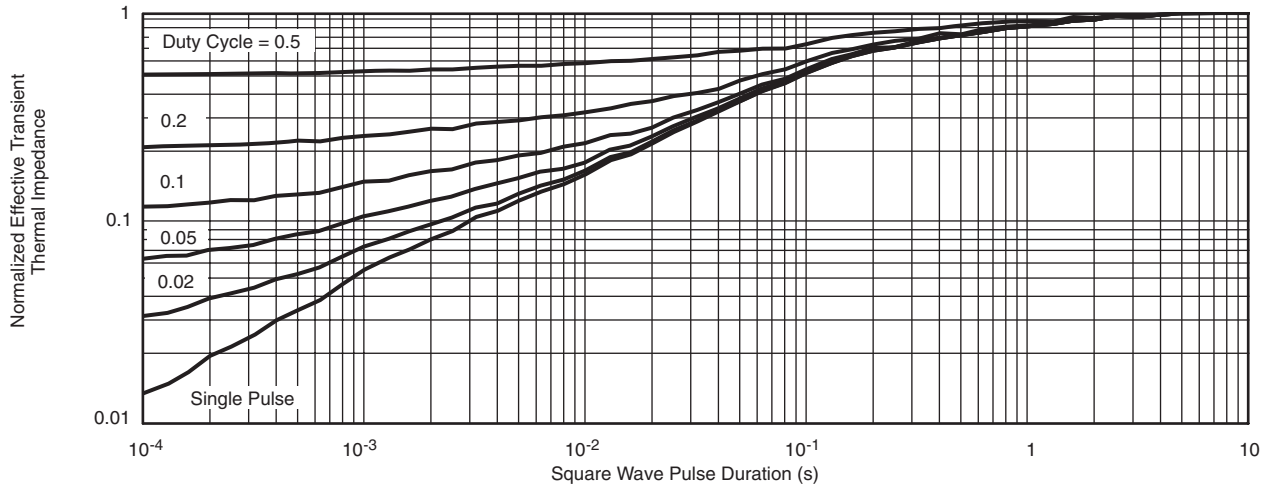
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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